MD.26. The deposition process of ZnO films doped with Eu and Title functionalized with Pd Authors Lupan Cristian; Trofim Viorel. Institution **Technical University of Moldova** Patent application entry number 1974, 2019 Patent no. The invention relates to the technology for deposition of semiconductor oxide films, in particular to the process of obtaining of ZnO:Eu³⁺ films, with application of rapid **Description** thermal annealing (T=650 °C, t=60s), with can be applied to the manufacture of gas sensors obtaining sensibility EN $S=I_{gas}/I_{air}=1.3$ for 100 ppm H_2 gas at room temperature and $S = I_{gas}/I_{air} = 118$ at operating temperature of 250 °C.

Class no. 12. Safety, protection and rescue of people

INTERNATIONAL EXHIBITS